

List of Publications by Year in descending order

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13
papers

2,267
citations

758635

12
h-index

1125271

13
g-index

13
all docs

13
docs citations

13
times ranked

4361
citing authors

#	ARTICLE	IF	CITATIONS
1	Near-Infrared, Self-Powered and Polarization-Sensitive Photodetector Based on GeSe ₂ /MoTe ₂ n Heterojunction. <i>Advanced Materials Interfaces</i> , 2022, 9, .	1.9	18
2	2D WS ₂ Based Asymmetric Schottky Photodetector with High Performance. <i>Advanced Electronic Materials</i> , 2021, 7, 2000964.	2.6	68
3	High-Performance Broadband Photodetectors Based on n-MoS ₂ /p-Ge _{0.9} Sn _{0.1} Heterojunctions. <i>ACS Applied Electronic Materials</i> , 2021, 3, 3218-3225.	2.0	10
4	Anti-ambipolar behavior and photovoltaic effect in p-MoTe ₂ /n-InSe heterojunctions. <i>Journal of Materials Chemistry C</i> , 2021, 9, 10372-10380.	2.7	24
5	An asymmetric contact-induced self-powered 2D In ₂ S ₃ photodetector towards high-sensitivity and fast-response. <i>Nanoscale</i> , 2020, 12, 7196-7205.	2.8	44
6	Self-assembly In ₂ Se ₃ /SnSe ₂ heterostructure array with suppressed dark current and enhanced photosensitivity for weak signal. <i>Science China Materials</i> , 2020, 63, 1560-1569.	3.5	24
7	Self-Powered SnS _{1-x} Se _x Alloy/Silicon Heterojunction Photodetectors with High Sensitivity in a Wide Spectral Range. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 40222-40231.	4.0	58
8	Tunable Polarity Behavior and High-Performance Photosensitive Characteristics in Schottky-Barrier Field-Effect Transistors Based on Multilayer WS ₂ . <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 2745-2751.	4.0	17
9	Various Structures of 2D Transition-Metal Dichalcogenides and Their Applications. <i>Small Methods</i> , 2018, 2, 1800094.	4.6	107
10	Tunable Schottky Barrier at MoSe ₂ /Metal Interfaces with a Buffer Layer. <i>Journal of Physical Chemistry C</i> , 2017, 121, 9305-9311.	1.5	45
11	Tunable Polarity Behavior and Self-Driven Photoswitching in WSe ₂ /WS ₂ Heterojunctions. <i>Small</i> , 2015, 11, 5430-5438.	5.2	114
12	Photoresponsive and Gas Sensing Field-Effect Transistors based on Multilayer WS ₂ Nanoflakes. <i>Scientific Reports</i> , 2014, 4, 5209.	1.6	377
13	Band offsets and heterostructures of two-dimensional semiconductors. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	1,361